HEWLETT-PACKARD COMPANY
Intellectual Property Administration
P. O. Box 272400
Fort Collins, Colorado 80527-2400

PATENT APPLICATION

ATTORNEY DOCKET NO. 200208229-1

IN THE
UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor(s): Richard L. Hilton et al. **Confirmation No.:**

Application No.: **Examiner:**

Filing Date: herewith **Group Art Unit:**

Title: MEMORY CELL STRINGS IN A RESISTIVE CROSS POINT MEMORY CELL ARRAY

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is submitted:

(X) under 37 CFR 1.97(b), or
(Within three months of filing national application; or date of entry of national application; or before mailing date of first office action on the merits; whichever occurs last)

( ) under 37 CFR 1.97(c) together with either a:
( ) Statement under 37 CFR 1.97(e), or
( ) a $180.00 fee under 37 CFR 1.17(p), or
(After the CFR 1.97 (b) time period, but before final action or notice of allowance, whichever occurs first)

( ) under 37 CFR 1.97 (d) together with a:
( ) Statement under 37 CFR 1.97(e)(1) or (2), and
( ) a $180.00 fee set forth in 37 CFR 1.17(p).
(Filed after final action, a notice of allowance, on or before payment of the issue fee)

Please charge to Deposit Account **08-2025** the sum of $0.00 . At any time during the pendency of this application, please charge any fees required or credit any overpayment to Deposit Account **08-2025** *pursuant to* 37 CFR 1.25.

(X) Applicant(s) submit herewith Form PTO 1449 - Information Disclosure Citation together with copies, of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s) may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 CFR 1.56.

( ) A concise explanation of the relevance of foreign language patents, foreign language publications and other foreign language information listed on PTO Form 1449, as presently understood by the individuals(s) designated in 37 CFR 1.56 (c) most knowledgeable about the content is given on the attached sheet, or where a foreign language patent is cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action which indicates the degree of relevance found by the foreign office is listed on form PTO 1449 and is enclosed herewith.

It is requested that the information disclosed herein be made of record in this application.

"Express Mail" label no. **ET891040777US**

Date of Deposit **July 7, 2003**

I hereby certify that this is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to: Commissioner for Patents, Alexandria, VA 22313-1450.

By _____

Typed Name: **Denyse Dauphinais**

Respectfully submitted,

Richard L. Hilton et al.

By _____

Matthew B. McNutt

Attorney/Agent for Applicant(s)
Reg. No. **39, 766**

Date: **July 7, 2003**

PATENT APPLICATION

Sheet 1 of 1

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. **200208229-1**	APPLICATION NO.	CONFIRMATION NO.
	APPLICANT **Richard L. Hilton et al.**		
	FILING DATE **herewith**	GROUP	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	1A	6,169,686B1	Jan. 2, 2001	Brug et al.	
	1B	6,259,644B1	Jul. 10, 2001	Tran et al.	
	1C	6,567,297 B2	May 20, 2003	R. Jacob Baker	
	1D	2002/0101758	Aug. 1, 2002	R. Jacob Baker	
	1E	2003/0039162	Feb. 27, 2003	R. Jacob Baker	
	1F				
	1G				
	1H				
	1I				
	1J				
	1K				

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L					
	1M					
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	1Q	"Nonvolatile RAM based on Magnetic Tunnel Junction Elements" by M. Durlam et al. 2000 IEEE International Solid-State Circuits Conference 07803-5853-8/00, Motorola Labs, Physical Sciences Research Labs, Tempe, AZ, Section TA 7.3
	1R	"A 10ns Read and Write Non-volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell" by Roy Scheuerlein et al. 2000 IEEE International Solid-State Circuits Conference 07803-5853-8/00, IBM Research Almaden Research Center, San Jose, CA, Section TA 7.2
	1S	"Offset Compensating Bit-Line Sensing Scheme for High Density DRAM's" by Yohi Watanabe et al., IEE Jurnal of Solid-State Circuits, Vol. 29, No. 1, January 1994.

EXAMINER	DATE CONSIDERED